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BRANCH: ELECTRONICS AND COMMUNICATION (B)

SUBJECT: ELECTRONIC DEVICES LAB . EC-202

## EXPERIMENT#1.

Aim of the Experiment: To construct a selicon (Si) pro junction diode and evaluate I-V characteristics of it using T-CAD tool.

Objective:

(i) Construct a silicon pre junction diode having n-type and p-type doping conventuation of 1×10'8/cc.

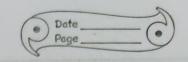
(ii) finding the I-V characteristics of the diode by varying voltage across diods by the IV to IV.

diode from - IV to IV.

Software Used: logenda Visual TCAD tool.

Theory: Diode is a 2-terminal device also known as p-n juntion diode and depending on its doping level can work in both journand bias and neveral bias mode. When the positive voltage terminal is connected to ptype junction, the diode is forward biased. In forward biased mode, after a certain voltage known as huee voltage, unvent flows injuntely ie the diode provides pro resistance. This line voltage is 0.3 V for Germanium and 0.7 V for silicon. When the negative voltage terminal is connected to ptype junction, it is neverse biased. In neverse bias mode, diode ideally provides injurite resistance and here no Teacher's Signature.

- (forward Bias). P (Catrode)
+ (Revense Bias).
pr junction diode Symbol. (Anode)



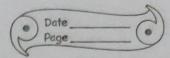
Useage is rentifier circuit to convent AC to DC, it can be used as a switch, voltage regulator.

## Procedure:

- O We will open the Visical TCAD tool by opening the terminal and goto the New file and Choose device drawing option. Awindow With black background will open up with default guid sparing width of 0.01 um.
- (2) We have to prepare a diode of (L=24m&H=24m) with anode of (L=14m&H=0.14m) and caltrode of (L=24m&H=0.14m).
- 3) With the help of shapes given on left top we will use neutangular shape to design the device.
- @ Add the negion label substrate (24mx24m) from the silicon material with the mesh size as 410 to of the block size & add amode & cathode with Aluminian
- Dow adding using Add Dopring profile we will make doping of the substrate. We dope the whole substrate with N-type / donor with the consistration of 1x10 18/cc. This doping is comfound doping. Then we do p-type doping in the upper half of the Substrate. P-type acceptor with the concentration of 2x10 16/cc. And this type of doping is gaussian doping.
- 6) Now with the option Do mesh we can mesh the device and negine the mesh with the option Regine existing mesh and make the arria of junction deusen after refuring 2 to 3 times

represent: To construct a history (61) of D. diffusion With 2x1018/co (Goussian) Depung / SUL SUBSTRATE) & characteristics of the deade by varying (-1,2) THOUSE OUR V WOUNDS (-1,2-1) DEVICE STRUCTURE of an junction diode Substrate doping: Ntype (donou): uniform doping: 1x1016/cc. n-diffusion: n'type (donou): unform doping: 1x1018/cc. p-diffussion: ptype (aneptor): gaussian doping: 2×10'8/cc.

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D'After the mesting being done we will save this file to . tif file using dervice option in werm bour and save mest to file option to be solerted. @ Now we goto duine simulation, from the folder below setup with the location open the tif file and it would take a little while to load. (2) We will apply biasing as contact warne "Anode", sommetype "Voltage Sweep" start Voltage = -1 V to stop Voltage = 1 V in step of 005. We now we sumulate inite the help of nun button, we firstly sowe it and then create a folder and choose this folder for simulation. Our simulation result, dat from the folder we have selected to simulate it. @ We plot the graph between Sanode & Vapp (anode). flout: The graph of Ianode Vs Vappianode) is drawn and it can be seen that bree voltage of the diode is approximately 0.7V.

Teacher's Signature.....

## Observation Table: At to course At to 1: approach and trement

		agentine Species Working
S. NO.	Vapp. (Anode_to_si_subst.) V.	I (prode to sisus.) A.
1.	0.005.	1.214e-20 minor
Ball 15.0	0.020	2.684e-20
My 3.1		4.812e-17
30 1 314.	with & low 600 00 00 of with	
5.	0.330	6.458 e-14
6.	(1-24 8H 00 4.00 H	9.417e-13
7.		1.697e-1110
8.	0.555	3.677 e-10
w.Pulopy olso	per on left top 0000.00 each week	2:085e-9.
10.	0.725.	2.58/2-7
11.	0.740	4.398 e-7
12.	16 (Sum 21/10 075.0116 all of	1.444e-6
13.	1000 0.800 W. do	4.4318-6
14.	0.815.	7.607e-6
15.	0.820 00 00000	9.6078-6
16.	No. 835 V No. 1	
17.		
18.	abolinate 009.0 miles	8.906e-5
19.	0.915	0:00013
20.	0.935	0.00017.
them extra option to much we can much the device of the		
	The same of the sa	N 14 26 2

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votabular votabler.

